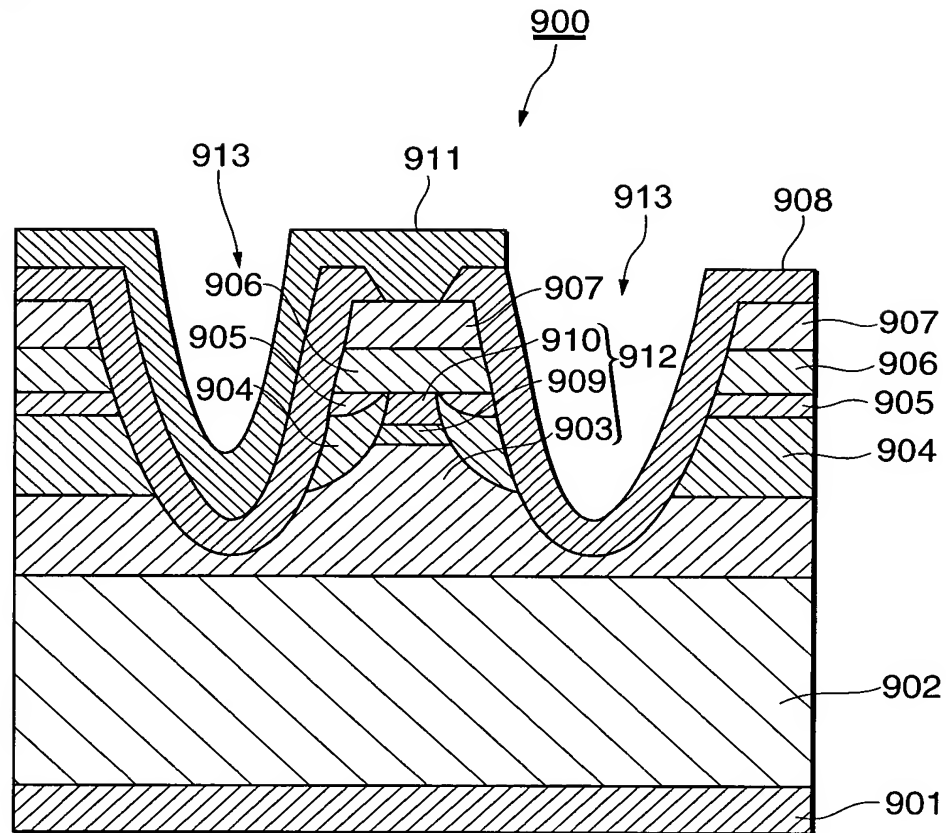


Fig.1

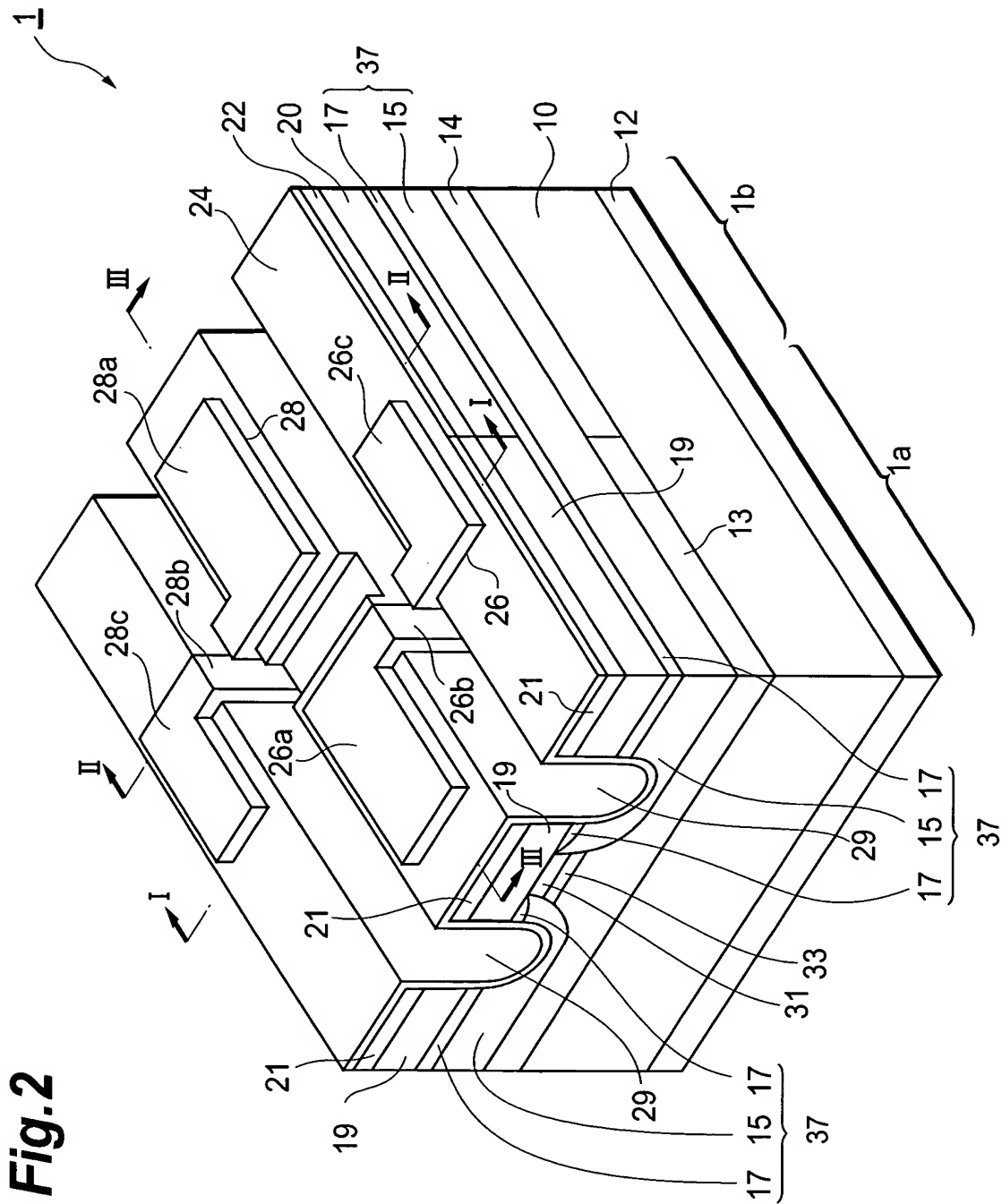


Fig.3

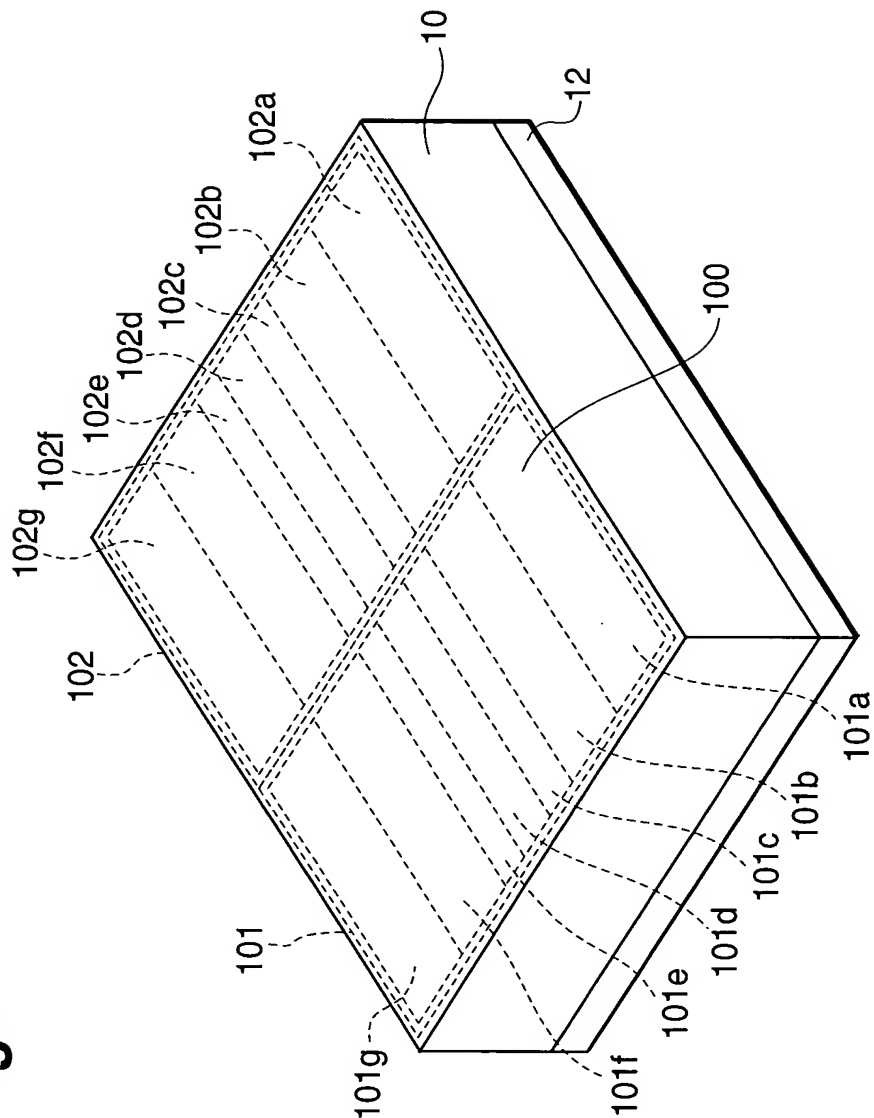


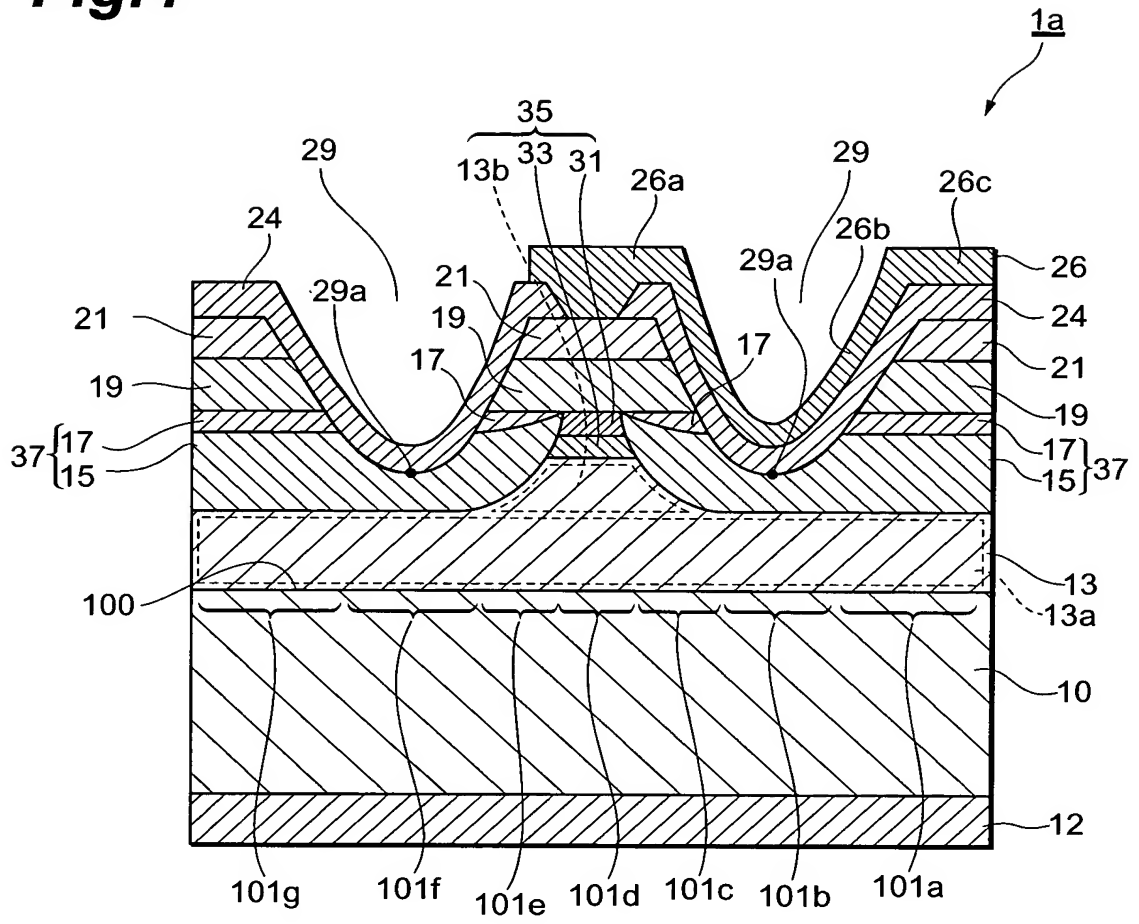
Fig.4

Fig.5

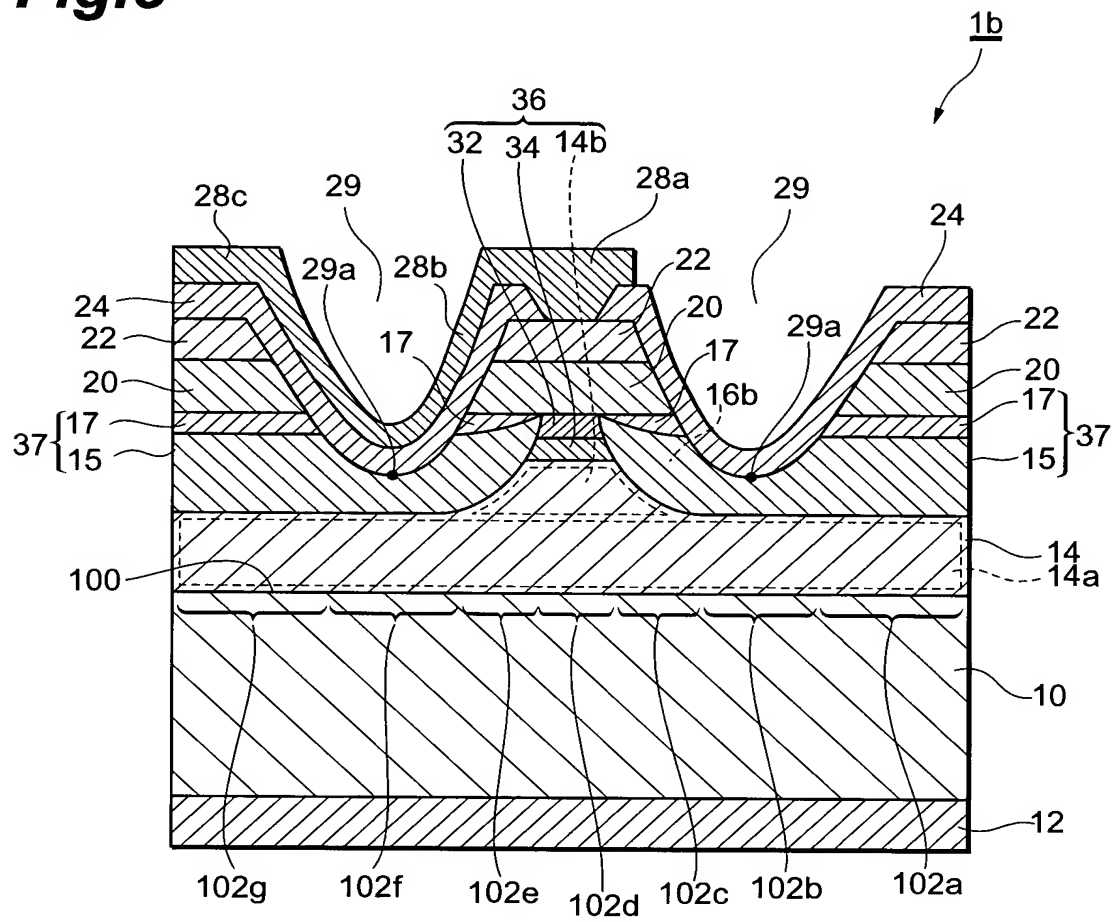
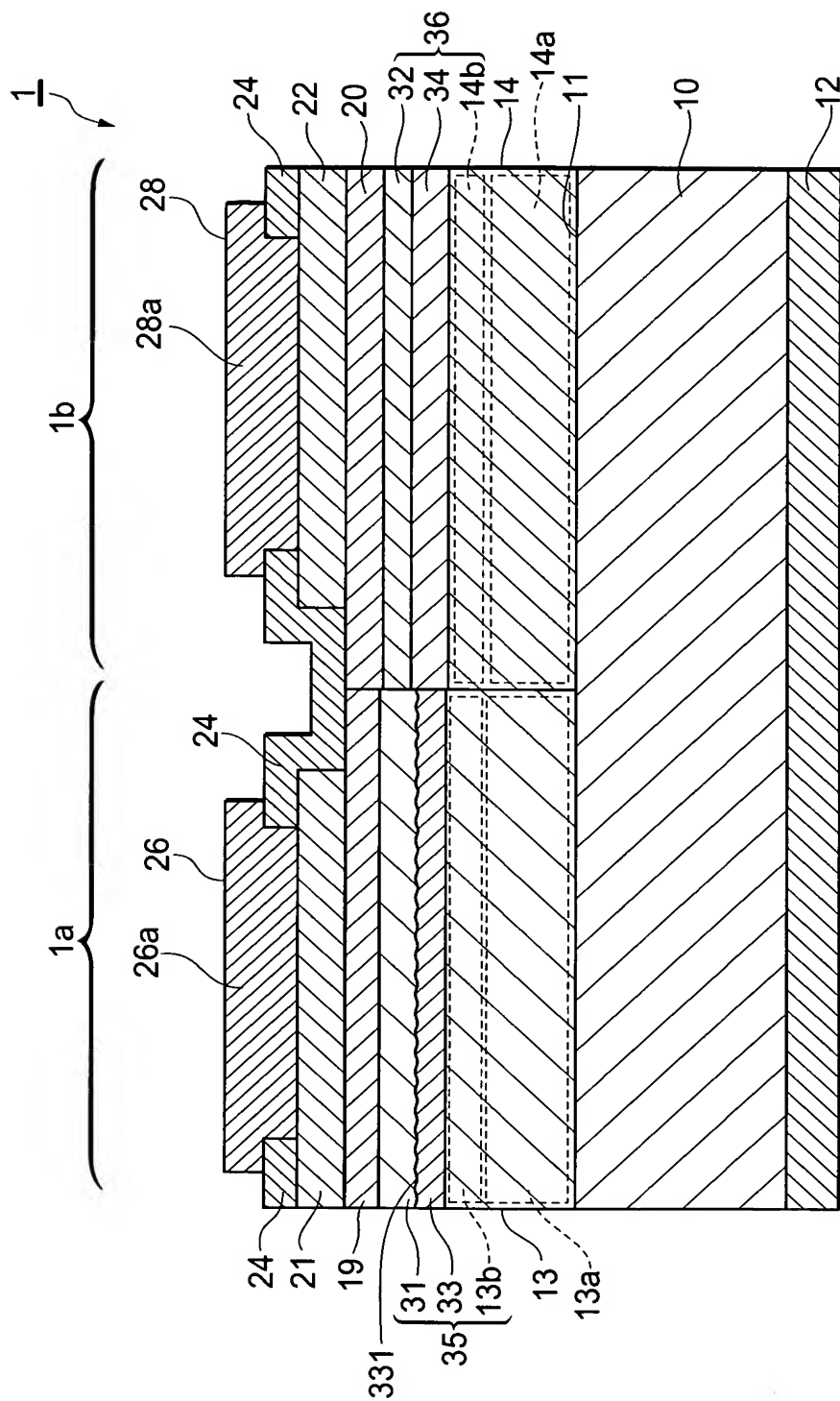


Fig.6



[illegible]

A cross-sectional view of a semiconductor device. The structure consists of a substrate 901, a base layer 902, and a patterned layer 903. On top of layer 903 is a wavy structure 904. This wavy structure has a central peak 905 and two side peaks 906. The central peak 905 is further divided into a top layer 907 and a bottom layer 909. The side peaks 906 are also divided into a top layer 907 and a bottom layer 909. The bottom layer 909 is labeled with 'A' and has a curved arrow indicating a direction. The top layer 907 is labeled with 'A' and has a curved arrow indicating a direction. The central peak 905 is labeled with 'A' and has a curved arrow indicating a direction. The side peaks 906 are labeled with 'A' and have a curved arrow indicating a direction. The wavy structure 904 is labeled with 'A' and has a curved arrow indicating a direction. The base layer 902 is labeled with 'A' and has a curved arrow indicating a direction. The substrate 901 is labeled with 'A' and has a curved arrow indicating a direction. The device is illuminated by light I_3 from the top and I_4 from the bottom. The central peak 905 has a height l_3 and the side peaks 906 have a height l_4 .

Fig.8A

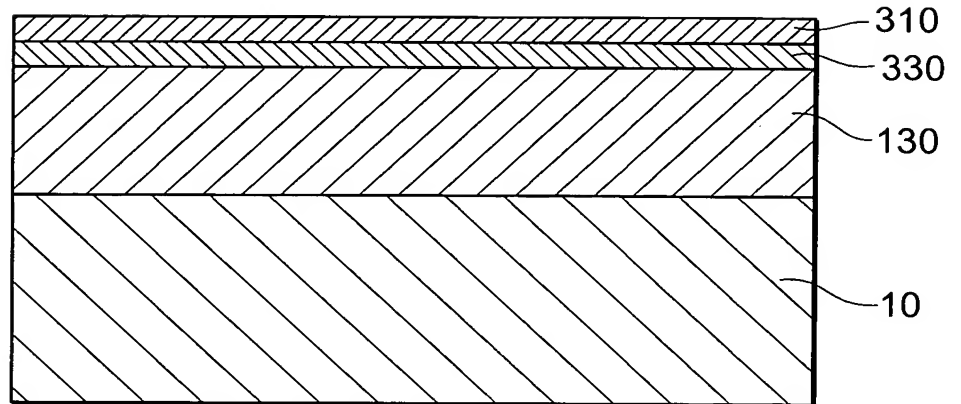


Fig.8B

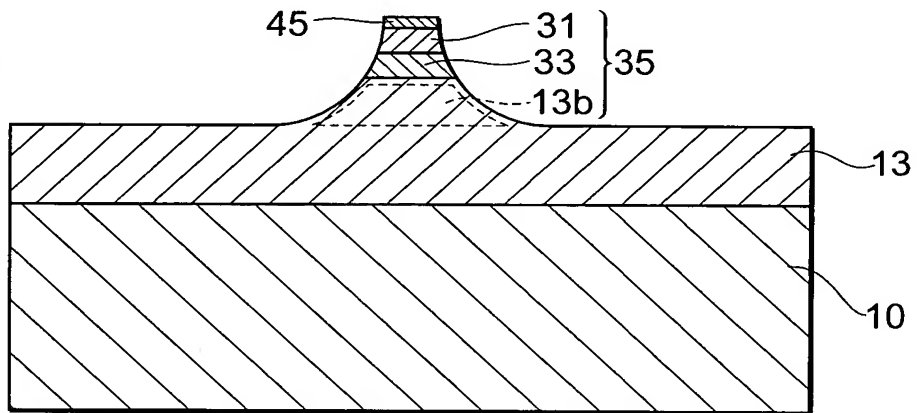


Fig.8C

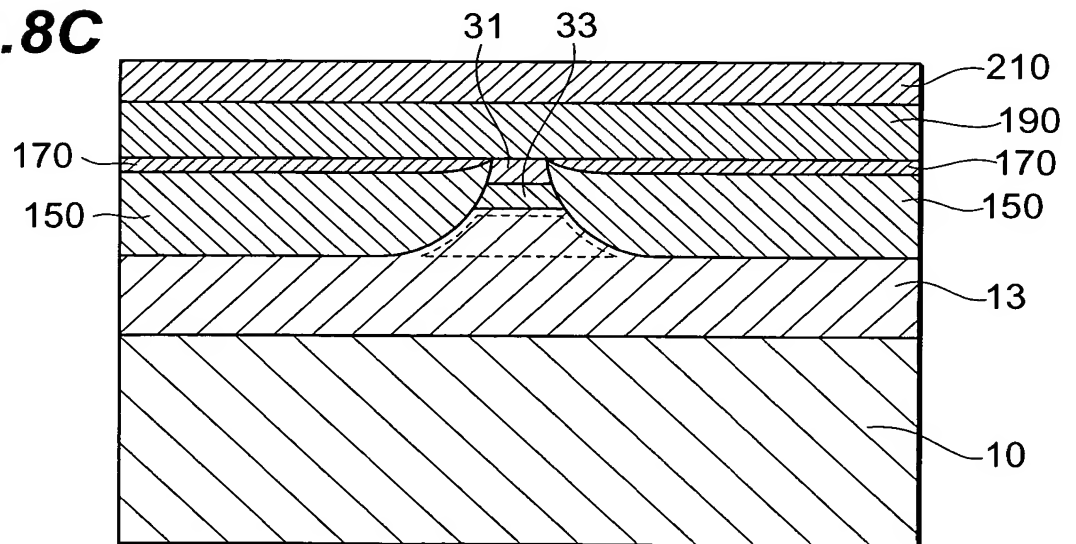


Fig.9A

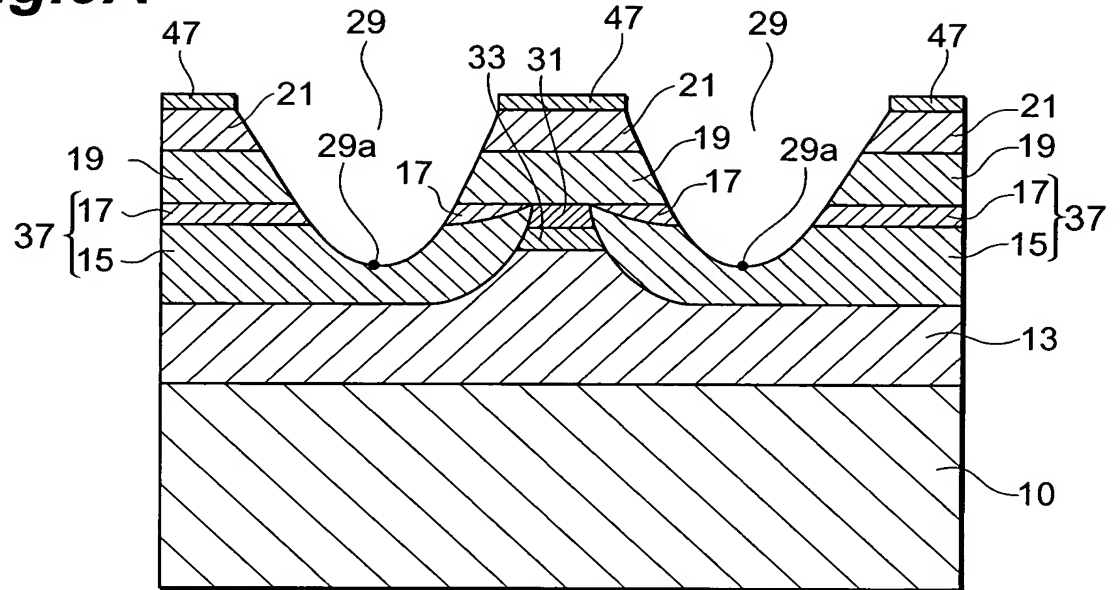


Fig.9B

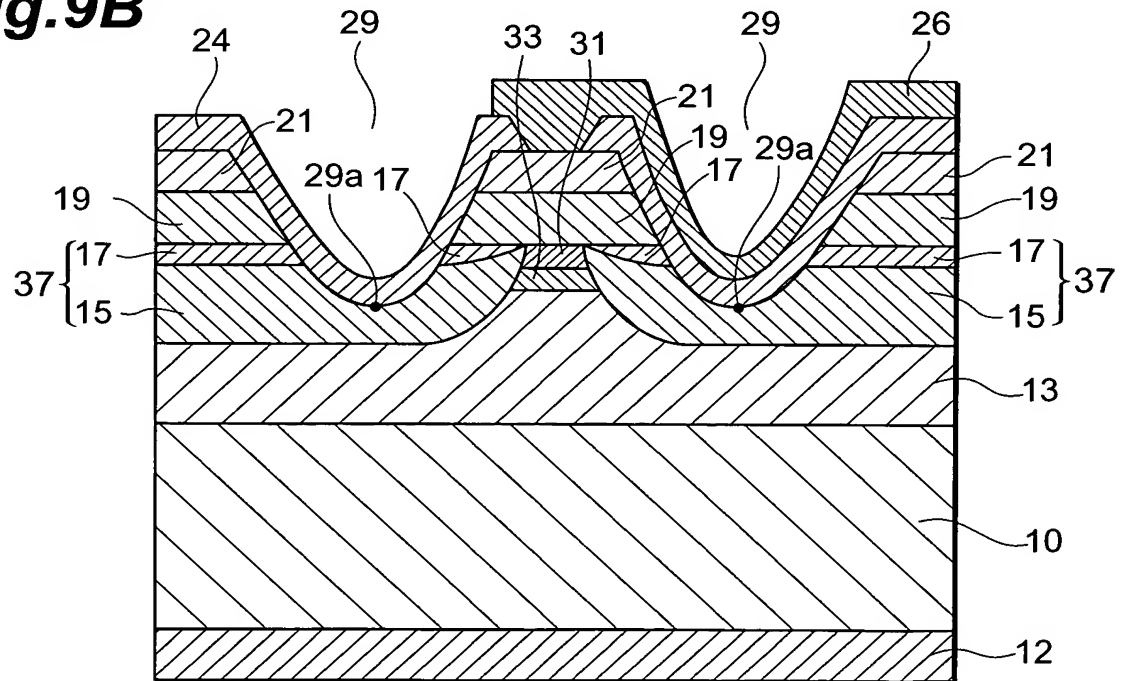


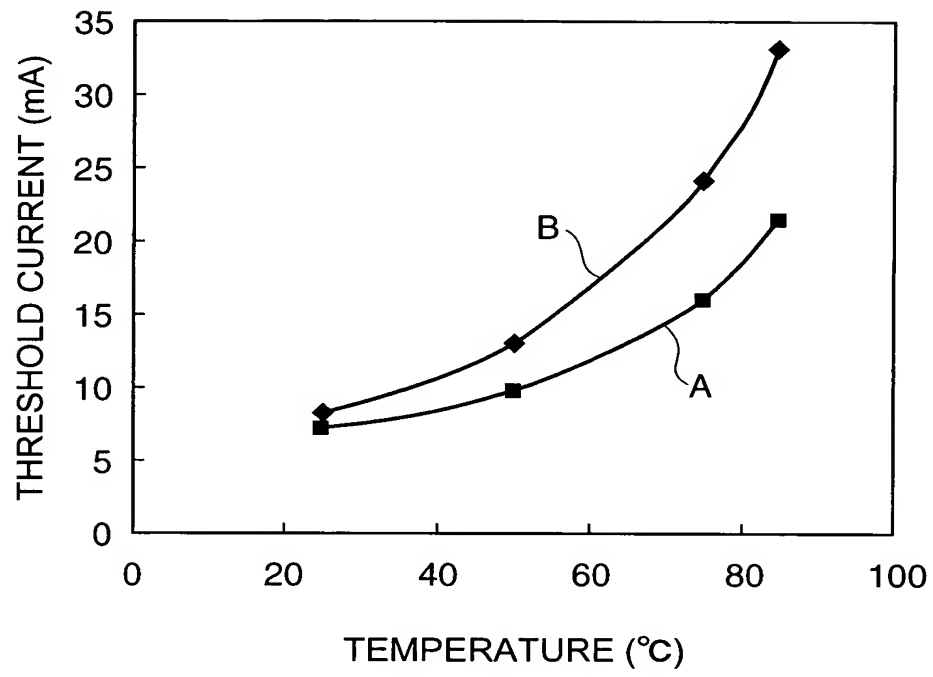
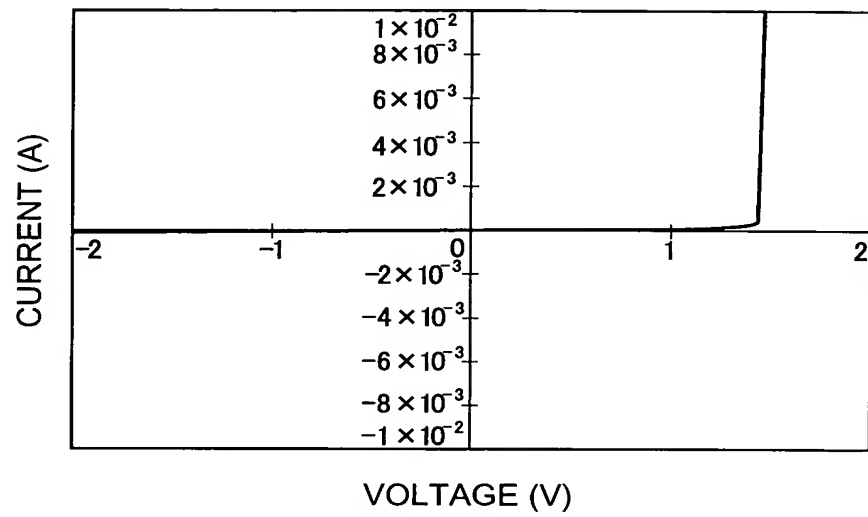
Fig.10

Fig.11A**Fig.11B**